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5.3.3 The Role of Leveler

Sommario/riassunto

Finding new materials for copper/low-k interconnects is critical to the continuing development of computer chips. While copper/low-k interconnects have served well, allowing for the creation of Ultra Large Scale Integration (ULSI) devices which combine over a billion transistors onto a single chip, the increased resistance and RC-delay at the smaller scale has become a significant factor affecting chip performance. Advanced Interconnects for ULSI Technology is dedicated to the materials and methods which might be suitable replacements. It covers a broad range of topics, from physical